

Fig. 1 (a) C-Vs of ALD-Al₂O₃ on p- and n-GaAs(001)-4x6.¹

Fig. 1 (b) C-Vs of ALD-Al₂O₃ on p- and n-In_{0.53}Ga_{0.47}As.²

Fig. 1 (c) C-Vs of ALD-HfO₂ on p- and n-In_{0.53}Ga_{0.47}As.²

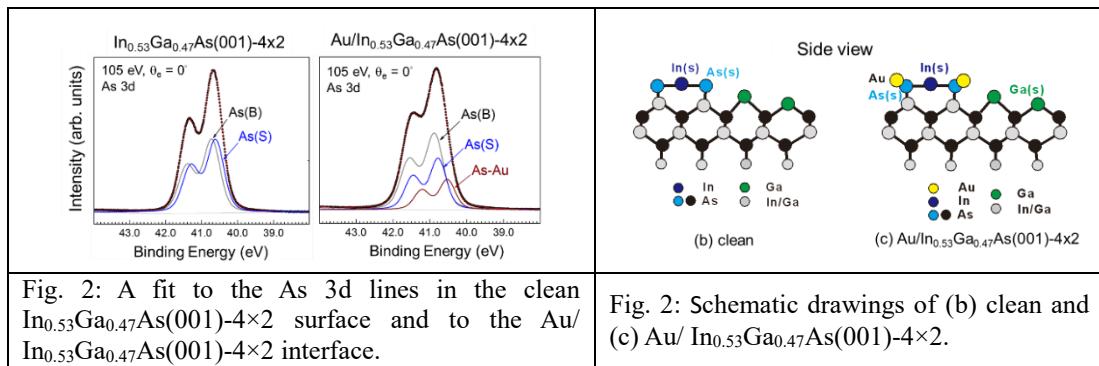


Fig. 2: A fit to the As 3d lines in the clean In_{0.53}Ga_{0.47}As(001)-4×2 surface and to the Au/In_{0.53}Ga_{0.47}As(001)-4×2 interface.

Fig. 2: Schematic drawings of (b) clean and (c) Au/In_{0.53}Ga_{0.47}As(001)-4×2.

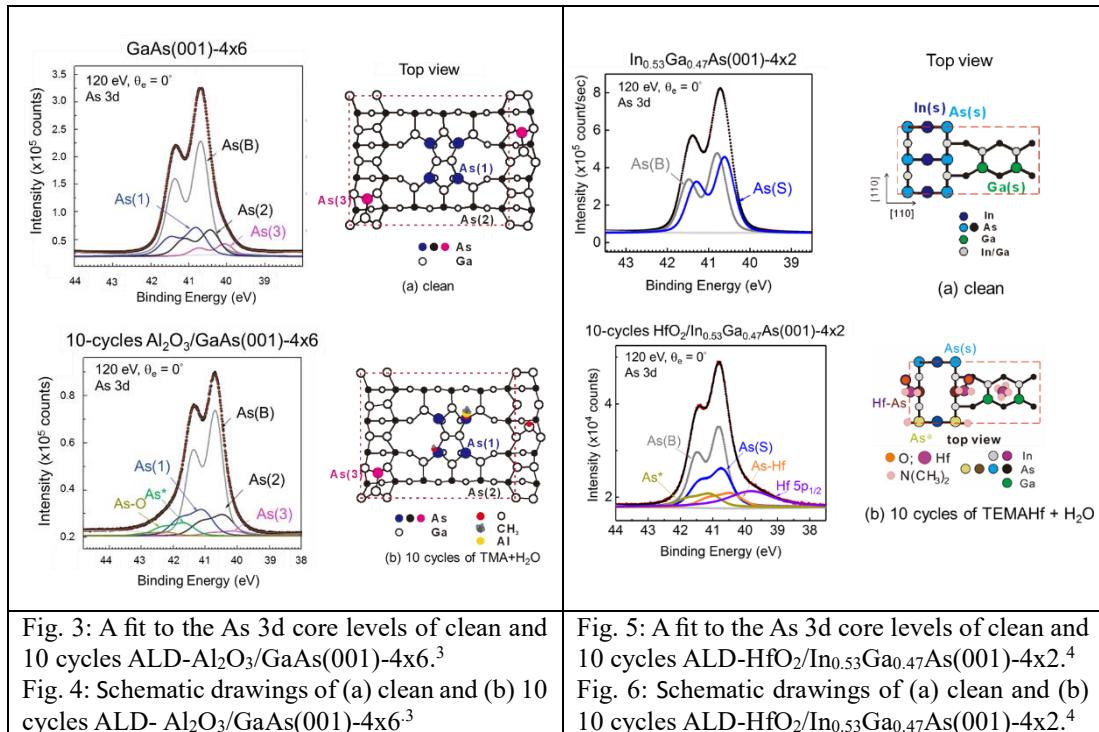


Fig. 3: A fit to the As 3d core levels of clean and 10 cycles ALD-Al₂O₃/GaAs(001)-4x6.³

Fig. 4: Schematic drawings of (a) clean and (b) 10 cycles ALD-Al₂O₃/GaAs(001)-4x6.³

Fig. 5: A fit to the As 3d core levels of clean and 10 cycles ALD-HfO₂/In_{0.53}Ga_{0.47}As(001)-4x2.⁴

Fig. 6: Schematic drawings of (a) clean and (b) 10 cycles ALD-HfO₂/In_{0.53}Ga_{0.47}As(001)-4x2.⁴

¹H. W. Wan, *et al.*, *J. Cryst. Growth* (2017), <http://dx.doi.org/10.1016/j.jcrysgro.2016.11.118>.

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